

In the Claims:

Claims 1-8 (canceled)

Claim 9 (currently amended): A method of forming an integrated circuit capacitor comprising the steps of:

providing a silicon substrate with a first dielectric film containing at least one copper layer;

forming an etch-stop/barrier layer over said first dielectric layer and said at least one copper layer, said etch-stop/barrier layer contacting said copper layer and formed using at least two different dielectric films;

forming a first conductive layer over said first dielectric layer, said first conductive layer contacting said etch-stop/barrier layer; and

removing a region of said first conductive layer such that a portion of said etch-stop/barrier layer remains between said first conductive layer and said copper layer, said first conductive layer, said etch-stop/barrier layer, and said copper layer forming a capacitor.

Claim 10 (previously presented): The method of claim 9 further comprising:

forming copper contacts to said first conductive layer; and

forming a second copper layer that electrically contacts said copper contacts.

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Claim 11 (previously presented): The method of claim 9 wherein said first conductive layer is formed from a material selected from the group consisting of aluminum, aluminum oxide, tantalum nitride, titanium nitride, tungsten, tungsten nitride, silicon carbide, and their alloys.

Claims 12- 17 (canceled)\